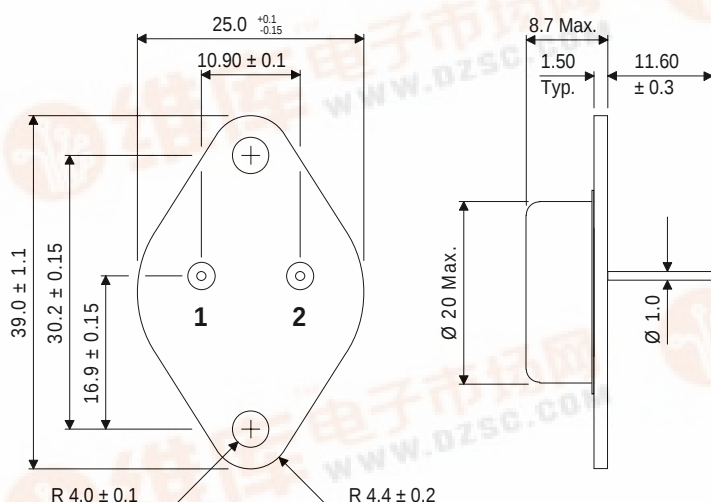
**BUZ907**
BUZ908**MECHANICAL DATA**

Dimensions in mm

**P-CHANNEL
POWER MOSFET****POWER MOSFETS FOR
AUDIO APPLICATIONS****FEATURES**

- HIGH SPEED SWITCHING
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (220V & 250V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODES
- COMPLIMENTARY N-CHANNEL BUZ902 & BUZ903

TO-3

Pin 1 – Gate

Pin 2 – Drain

Case – Source

ABSOLUTE MAXIMUM RATINGS(T_{case} = 25°C unless otherwise stated)

		BUZ907	BUZ908
V _{DSX}	Drain – Source Voltage	-220V	-250V
V _{GSS}	Gate – Source Voltage	±14V	
I _D	Continuous Drain Current	-8A	
I _{D(PK)}	Body Drain Diode	-8A	
P _D	Total Power Dissipation @ T _{case} = 25°C	125W	
T _{stg}	Storage Temperature Range	-55 to 150°C	
T _j	Maximum Operating Junction Temperature	150°C	
R _{θJC}	Thermal Resistance Junction – Case	1°C/W	

STATIC CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
BV _{DSX} Drain – Source Breakdown Voltage	V _{GS} = 10V I _D = -10mA	BUZ907	-220			V
		BUZ908	-250			V
BV _{GSS} Gate – Source Breakdown Voltage	V _{DS} = 0	I _G = ±100μA	±14			V
V _{GS(OFF)} Gate – Source Cut-Off Voltage	V _{DS} = -10V	I _D = -100mA	-0.15		-1.5	V
V _{DS(SAT)} * Drain – Source Saturation Voltage	V _{GD} = 0	I _D = -8A			-12	V
R _{DS(on)} * Static – Source Resistance	V _{GS} = -10	I _D = -8A			1.5	Ω
I _{DSX} Drain – Source Cut-Off Current	V _{GS} = 10V	V _{DS} = -220V BUZ907			-10	mA
		V _{DS} = -250V BUZ908			-10	mA
y _{fs} * Forward Transfer Admittance	V _{DS} = -10V	I _D = -3A	0.7		2	S

DYNAMIC CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
C _{iss} Input Capacitance	V _{DS} = -10V f = 1MHz			TBA		pF
C _{oss} Output Capacitance				TBA		
C _{rss} Reverse Transfer Capacitance				TBA		
t _{on} Turn-on Time	V _{DS} = -20V I _D = -5A			TBA		ns
t _{off} Turn-off Time				TBA		

* Pulse Test: Pulse Width = 300μs , Duty Cycle ≤ 2%.

